



LIGITEK

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★ BAR DIGIT LED DISPLAY

LBD1B2A-XX

DATA SHEET

DOC. NO : QW0905-LBD1B2A-XX

REV. : A

DATE : 20 - Apr. - 2006



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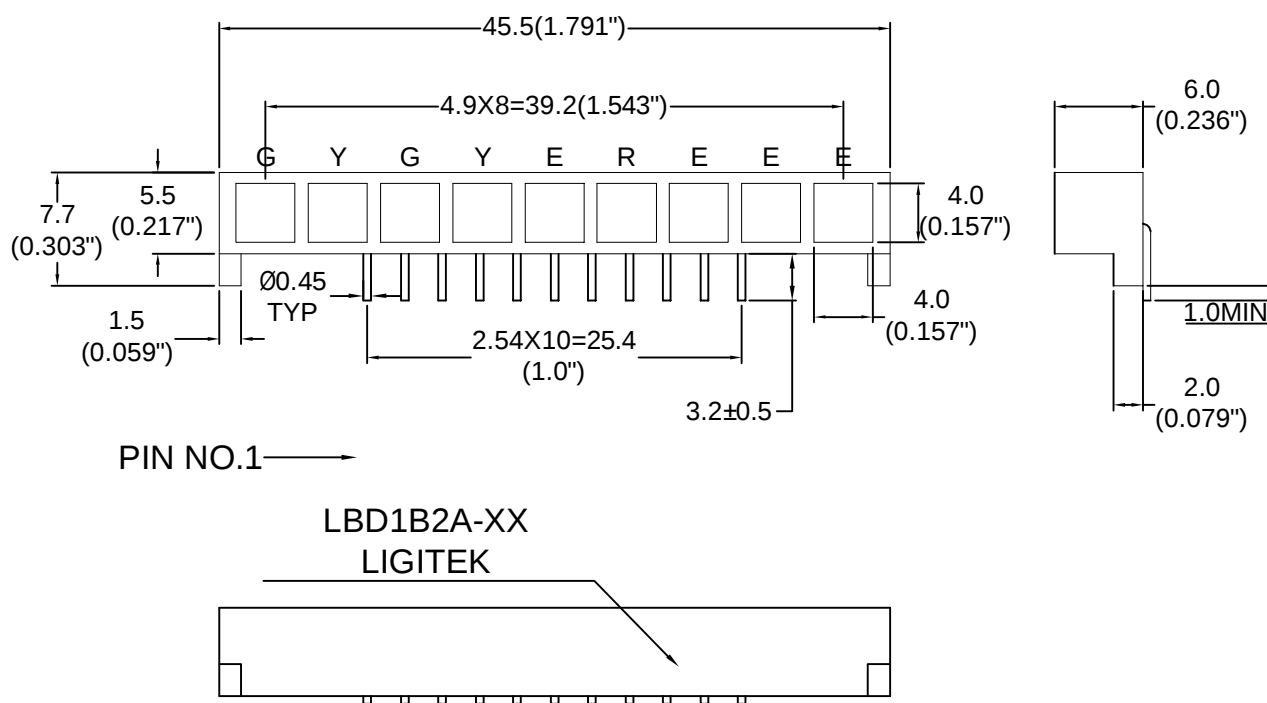
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PART NO. LBD1B2A-XX

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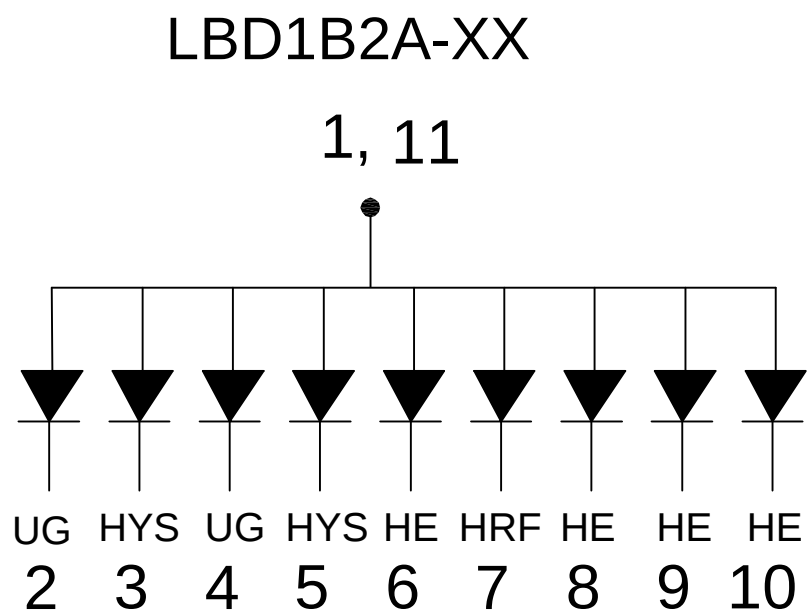
Package Dimensions



Note : 1.All dimension are in millimeters and (Inch) tolerance is $\pm 0.25\text{mm}$ unless otherwise noted.
2.Specifications are subject to change without notice.



Internal Circuit Diagram





Electrical Connection

PIN NO.1	LBD1B2A-XX
1	Common Anode
2	Cathode Green
3	Cathode Yellow
4	Cathode Green
5	Cathode Yellow
6	Cathode Orange
7	Cathode Red
8	Cathode Orange
9	Cathode Orange
10	Cathode Orange
10	Common Anode



Absolute Maximum Ratings at Ta=25 °C

Parameter	Symbol	Ratings				UNIT
		UG	HYS	HE	HRF	
Forward Current Per Chip	IF	30	30	30	30	mA
Peak Forward Current PerChip (Duty 1/10,0.1ms Pulse Width)	IFP	120	60	60	90	mA
Power Dissipation Per Chip	PD	100	75	75	75	mW
Reverse Current Per Any Chip	Ir	10				μA
Electrostatic Discharge(*)	ESD	2000				μA
Operating Temperature	Topr	-40 ~ +85				℃
Storage Temperature	Tstg	-40 ~ +85				℃
Solder Temperature 1/16 Inch Below Seating Plane For 3 Seconds At 260 ℃						

Part Selection And Application Information(Ratings at 25°C)

PART NO	CHIP		common cathode or anode	λ D (nm)	$\Delta \lambda$ (nm)	Electrical					IV-M
	Material	Emitted				Vf(v)			Iv(mcd)		
						Min.	Typ.	Max.	Min.	Typ.	
LBD1B2A-XX	AlGaInP	Green	Common Anode	574	20	1.7	2.1	2.6	10.5	18	2:1
	AlGaInP	Yellow		587	15	1.7	2.1	2.6	21.5	35	2:1
	AlGaInP	Orange		620	17	1.7	2.1	2.6	10.5	21.5	2:1
	AlGaInP	Red		630	20	1.5	1.7	2.4	21.5	35	2:1

Note : 1.The forward voltage data did not including ±0.1V testing tolerance.
2. The luminous intensity data did not including ±15% testing tolerance.

**Test Condition For Each Parameter**

Parameter	Symbol	Unit	Test Condition
Forward Voltage Per Chip	V _f	volt	I _f =20mA
Luminous Intensity Per Chip	I _v	mcd	I _f =10mA
Dominant Wavelength	λ D	nm	I _f =20mA
Spectral Line Half-Width	$\Delta \lambda$	nm	I _f =20mA
Reverse Current Any Chip	I _r	μ A	V _r =5V
Luminous Intensity Matching Ratio	IV-M		



Typical Electro-Optical Characteristics Curve

UG CHIP

Fig.1 Forward current vs. Forward Voltage

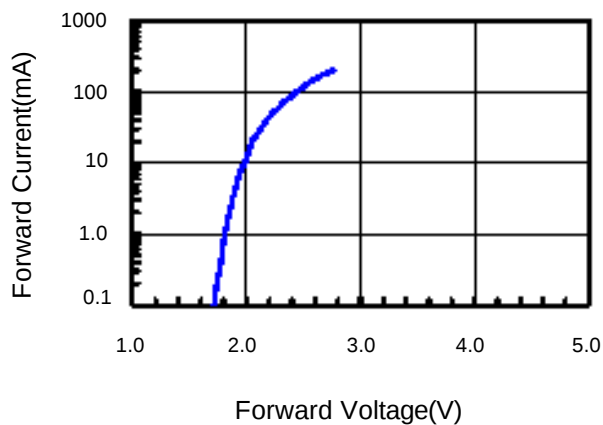


Fig.2 Relative Intensity vs. Forward Current

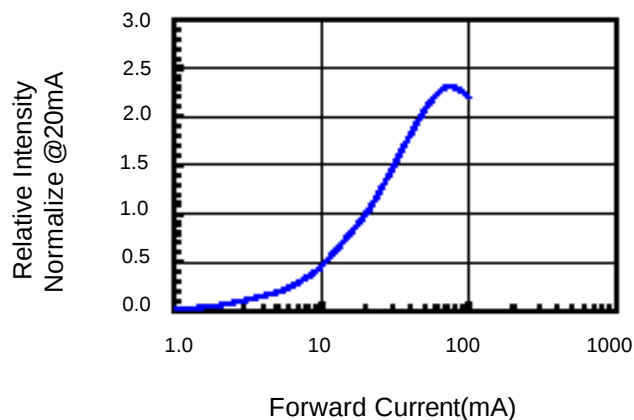


Fig.3 Forward Voltage vs. Temperature

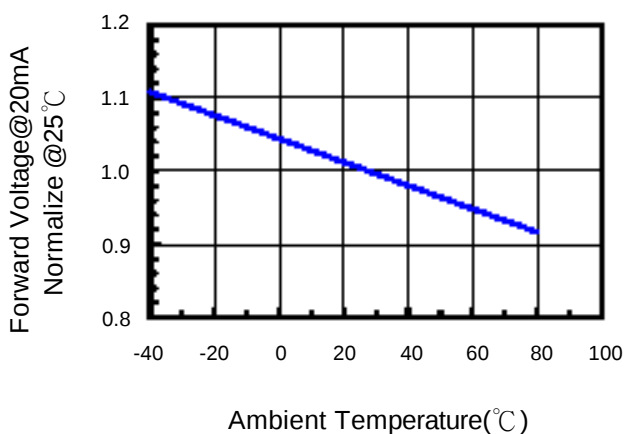


Fig.4 Relative Intensity vs. Temperature

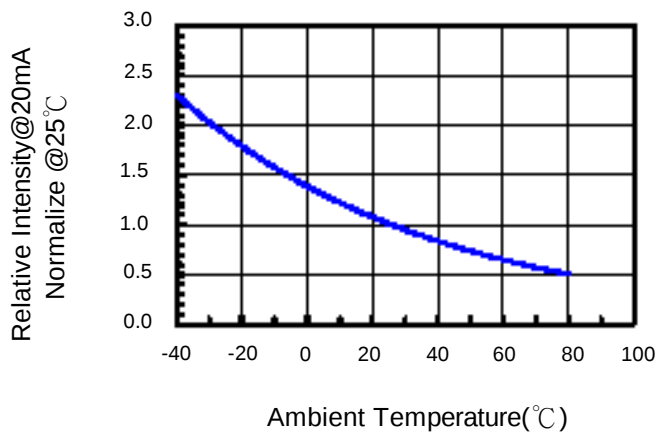
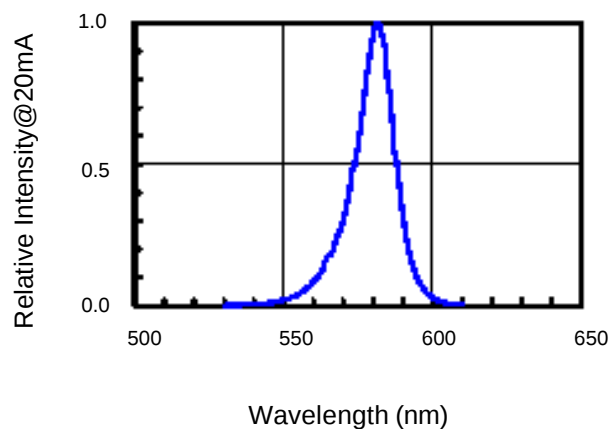


Fig.5 Relative Intensity vs. Wavelength





Typical Electro-Optical Characteristics Curve

HYS CHIP

Fig.1 Forward current vs. Forward Voltage

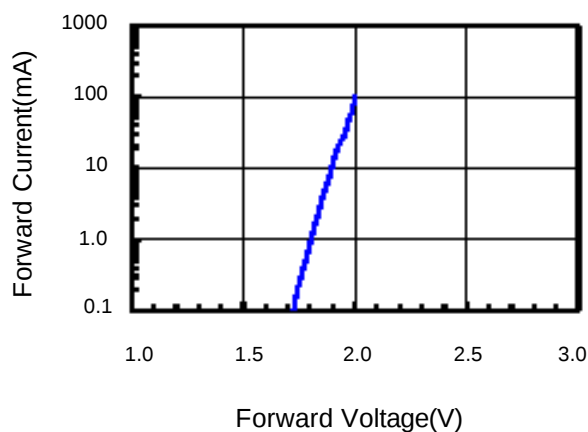


Fig.2 Relative Intensity vs. Forward Current

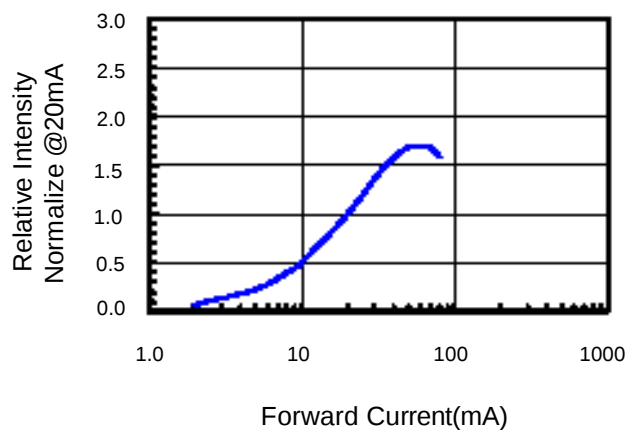


Fig.3 Forward Voltage vs. Temperature

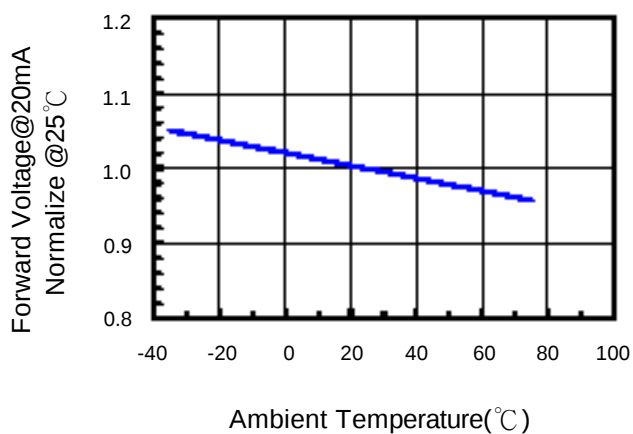


Fig.4 Relative Intensity vs. Temperature

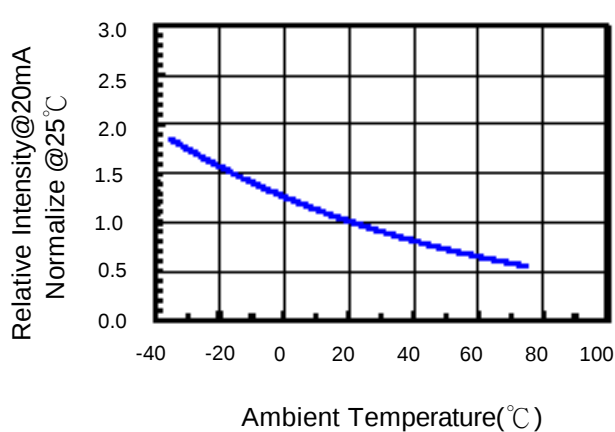
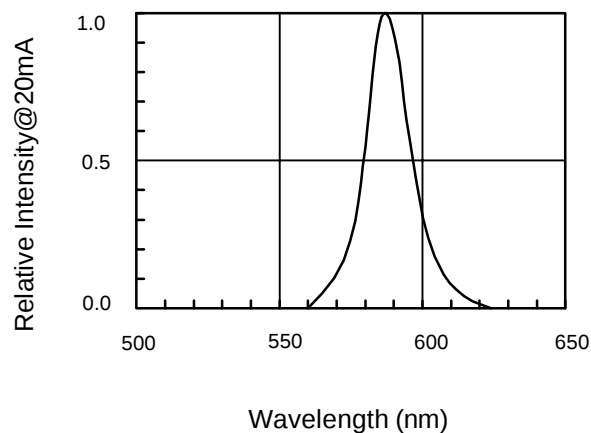


Fig.5 Relative Intensity vs. Wavelength





Typical Electro-Optical Characteristics Curve HE CHIP

Fig.1 Forward current vs. Forward Voltage

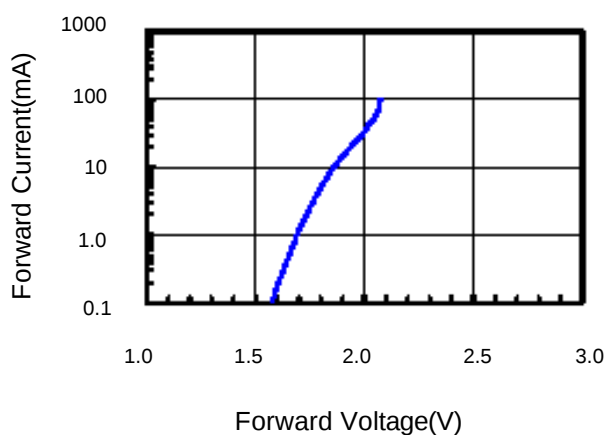


Fig.2 Relative Intensity vs. Forward Current

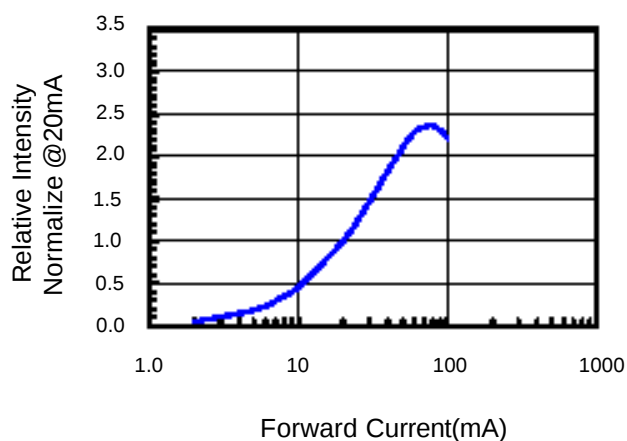


Fig.3 Forward Voltage vs. Temperature

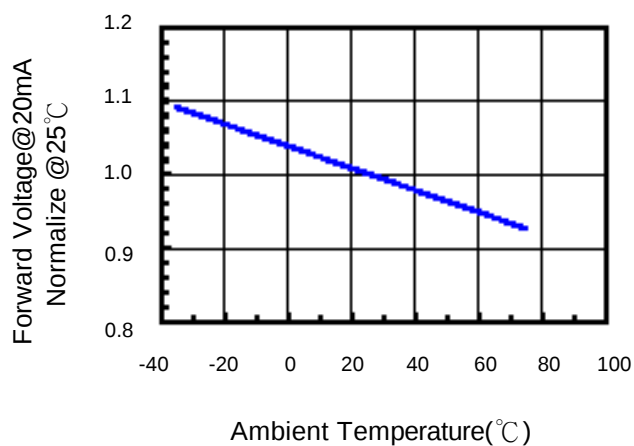


Fig.4 Relative Intensity vs. Temperature

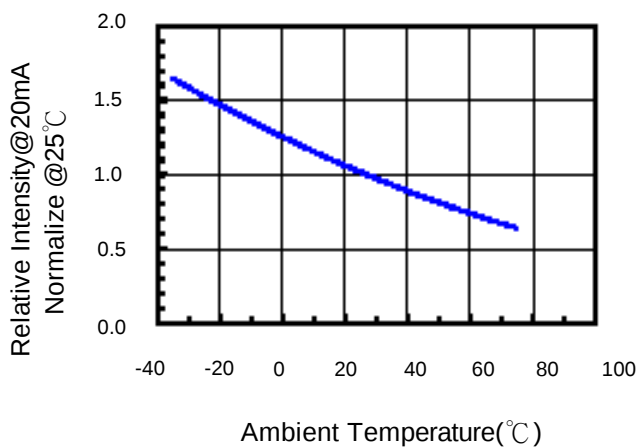
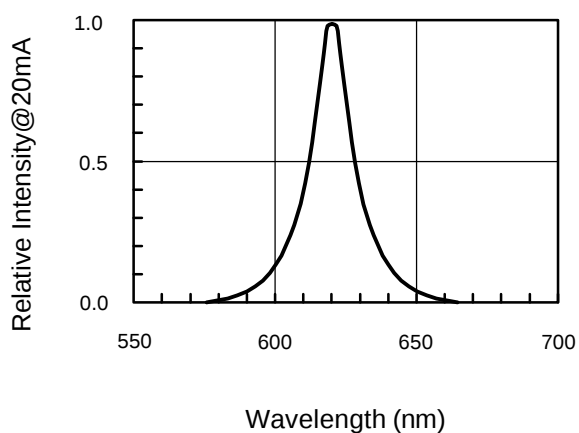


Fig.5 Relative Intensity vs. Wavelength





Typical Electro-Optical Characteristics Curve

HRF CHIP

Fig.1 Forward current vs. Forward Voltage

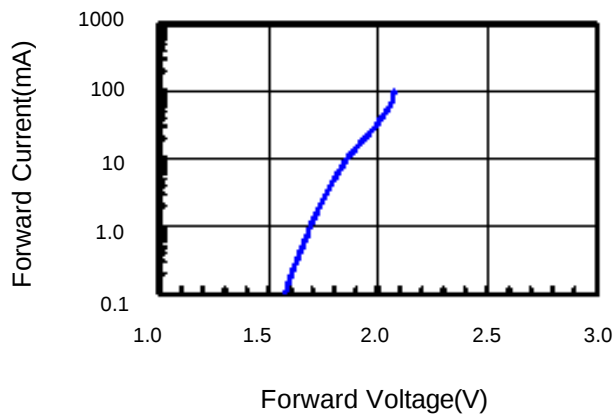


Fig.2 Relative Intensity vs. Forward Current

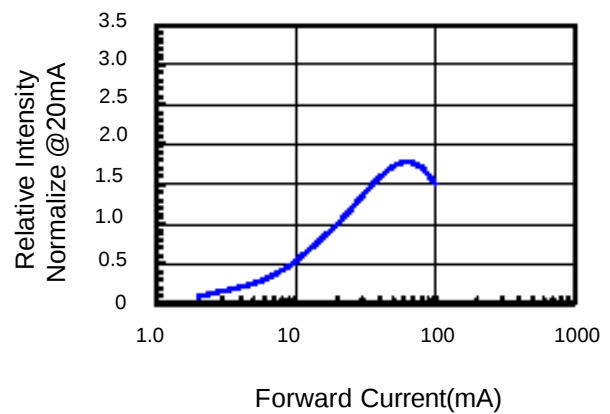


Fig.3 Forward Voltage vs. Temperature

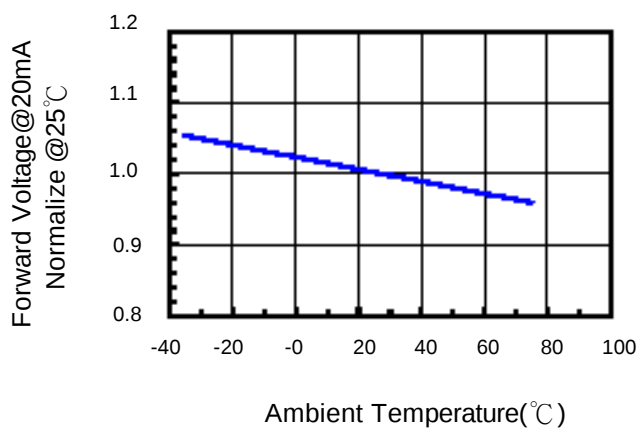


Fig.4 Relative Intensity vs. Temperature

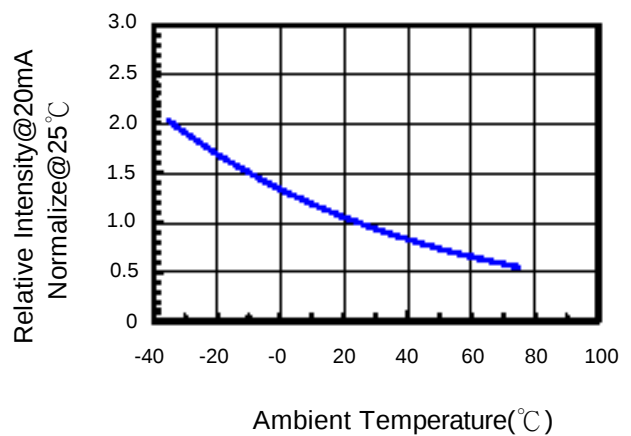
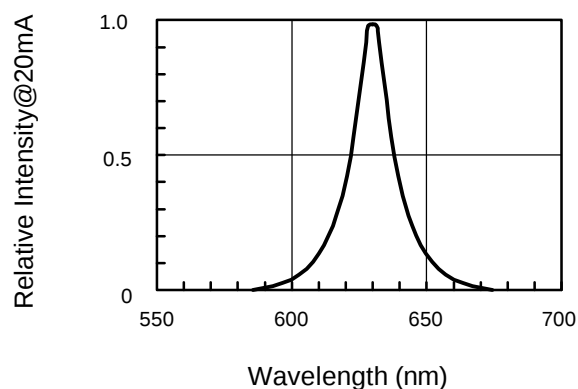


Fig.5 Relative Intensity vs. Wavelength



**Reliability Test:**

Test Item	Test Condition	Description	Reference Standard
Operating Life Test	1.Under Room Temperature 2.If=10mA 3.t=1000 hrs (-24hrs, +72hrs)	This test is conducted for the purpose of determining the resistance of a part in electrical and thermal stressed.	MIL-STD-750: 1026 MIL-STD-883: 1005 JIS C 7021: B-1
High Temperature Storage Test	1.Ta=105 °C ±5°C 2.t=1000 hrs (-24hrs, +72hrs)	The purpose of this is the resistance of the device which is laid under condition of high temperature for hours.	MIL-STD-883:1008 JIS C 7021: B-10
Low Temperature Storage Test	1.Ta=-40 °C ±5°C 2.t=1000 hrs (-24hrs, +72hrs)	The purpose of this is the resistance of the device which is laid under condition of low temperature for hours.	JIS C 7021: B-12
High Temperature High Humidity Test	1.Ta=65 °C ±5°C 2.RH=90 %~95% 3.t=240hrs ±2hrs	The purpose of this test is the resistance of the device under tropical for hours.	MIL-STD-202:103B JIS C 7021: B-11
Thermal Shock Test	1.Ta=105 °C ±5°C & -40 °C ±5°C (10min) (10min) 2.total 10 cycles	The purpose of this is the resistance of the device to sudden extreme changes in high and low temperature.	MIL-STD-202: 107D MIL-STD-750: 1051 MIL-STD-883: 1011
Solder Resistance Test	1.T.Sol=260 °C ±5°C 2.Dwell time= 10 ±1sec.	This test intended to determine the thermal characteristic resistance of the device to sudden exposures at extreme changes in temperature when soldering the lead wire.	MIL-STD-202: 210A MIL-STD-750: 2031 JIS C 7021: A-1
Solderability Test	1.T.Sol=230 °C ±5°C 2.Dwell time=5 ±1sec	This test intended to see soldering well performed or not.	MIL-STD-202: 208D MIL-STD-750: 2026 MIL-STD-883: 2003 JIS C 7021: A-2